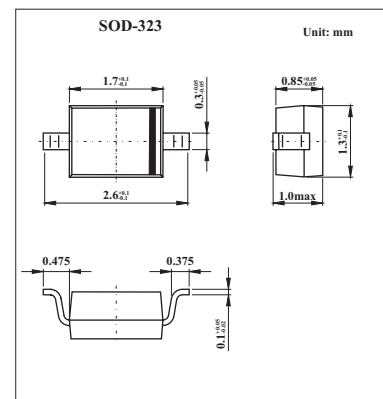


Schottky barrier Diodes

1PS76SB40

■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package
- Low diode capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	V_R			4	V
continuous forward current	I_F			120	mA
repetitive peak forward current	I_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		120	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		200	mA
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			150	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	CONDITIONS	MAX	UNIT
continuous forward voltage	V_F	$I_F = 1 \text{ mA}$	380	mV
		$I_F = 10 \text{ mA}$	500	mV
		$I_F = 40 \text{ mA}$	1	V
continuous reverse current	I_R	$V_R = 30 \text{ V}; \text{note 1};$	1	μA
		$V_R = 40 \text{ V}; \text{note 1};$	10	μA
diode capacitance	C_d	$V_R = 0 \text{ V}; f = \text{MHz};$	5	pF
thermal resistance from junction to ambient	R_{thj-a}		450	K/W

Note:

1. Pulse test: $t_p = 300 \mu\text{s}; \delta = 0.02$.

■ Marking

Marking	s4
---------	----